

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L10	97	257/197.ccls. and ((back or backside) with (gate or electrode or conductor or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:07
L11	206	(257/526).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:10
L12	178	257/565.ccls. and ((inversion or charge) with (layer or region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:22
L14	1625	(257/587 or 257/592).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:49
L15	5	(257/587 or 257/592).ccls. and (back near2 gate or backgate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 11:49
L16	142	(257/E29.171,E29.183,E29.189,E29.19,E29.198).ccls. and ((back near4 (electrode or gate or conductor)) or backgate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/01/22 11:55
L17	224	semiconductor and (((back\$4 or buried) with (gate or electrode)) and inversion and (vertical\$5 with bipolar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:01
L18	219	semiconductor and (((back or buried) with (gate or electrode)) or backgate) and inversion and (vertical\$5 with bipolar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:02

## EAST Search History

L19	1468	semiconductor and (((back or buried) with (gate or electrode)) or backgate) and inversion and (bipolar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:03
L20	195	semiconductor and (((back or buried) with (gate or electrode)) or backgate) and (inversion or accumulat\$5) and (vertical\$4 near5 bipolar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:02
L21	16	semiconductor and (((back or buried) with (gate or electrode)) or backgate) and inversion and (bipolar) and (collector with intrinsic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 12:03